

1 1. A method comprising:
 2 forming an integrated inductor over a substrate;
 3 forming an aperture underneath said inductor
 4 through said substrate from the back side of said
 5 substrate; and
 6 filling said aperture with a dielectric material.

1 2. The method of claim 1 including covering the
 2 backside of said substrate with a dielectric material.

1 3. The method of claim 2 including filling said
 2 aperture and covering said substrate back side with the
 3 same dielectric material.

1 4. The method of claim 1 including forming a field
 2 oxide formed over said substrate and forming said inductor
 3 over said field oxide region.

1 5. The method of claim 1 including forming said
 2 aperture completely through said substrate.

1 6. The method of claim 5 including supporting said
 2 inductor over said aperture in said substrate on an
 3 intervening layer between said substrate and said inductor.

1 7. A method comprising:
2 forming a layer over a substrate;
3 forming an integrated inductor over said layer
4 and said substrate;
5 forming an aperture underneath said inductor
6 completely through said substrate from the back side of
7 said substrate; and
8 filling said aperture with a dielectric material.

1 8. The method of claim 7 including covering the back
2 side of said substrate with a dielectric material.

1 9. The method of claim 8 including filling said
2 aperture and covering said substrate back side with the
3 same dielectric material.

1 10. The method of claim 7 wherein forming said layer
2 over said substrate includes forming a field oxide over
3 said substrate and forming said inductor over said field
4 oxide.

1 11. The method of claim 7 including forming said
2 aperture completely through said substrate to said layer.

1 12. The method of claim 11 including supporting said
2 inductor over said aperture and said substrate on said
3 layer.

1 13. An integrated circuit comprising:
2 a substrate;
3 an integrated inductor formed over a first side
4 of said substrate;
5 an aperture formed in said substrate from a
6 second side of said substrate underneath said inductor; and
7 a dielectric material formed in said aperture.

1 14. The circuit of claim 13 including an intervening
2 layer between said inductor and said substrate.

1 15. The circuit of claim 14 wherein said intervening
2 layer is a field oxide region.

1 16. The circuit of claim 14 wherein said aperture is
2 formed completely through said substrate to said
3 intervening layer.

1 17. The circuit of claim 16 wherein said aperture
2 encompasses the entire region beneath said integrated
3 inductor.

1 18. An integrated circuit comprising:
 2 a substrate;
 3 an inductor formed over a first side of said
 4 substrate;
 5 an aperture formed in said substrate from a
 6 second side of said substrate underneath said inductor and
 7 extending completely through said substrate from said
 8 second side of said substrate to said first side of said
 9 substrate;
 10 a dielectric material filling said aperture;
 11 a dielectric material also coating the back side
 12 of said substrate; and
 13 an intervening layer between said inductor and
 14 said substrate.

1 19. The circuit of claim 18 wherein said intervening
 2 layer is a field oxide region.

1 20. The circuit of claim 19 wherein said aperture
 2 encompasses the entire region beneath said integrated
 3 inductor.